

74AHC377; 74AHCT377

Octal D-type flip-flop with data enable; positive-edge trigger

Rev. 02 — 12 June 2008

Product data sheet

1. General description

The 74AHC377; 74AHCT377 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7-A.

The 74AHC377; 74AHCT377 has eight edge-triggered, D-type flip-flops with individual D inputs and Q outputs. A common clock input (CP) loads all flip-flops simultaneously when the data enable input ($\bar{E}$) is LOW. The state of each D input, one set-up time before the LOW-to-HIGH clock transition, is transferred to the corresponding output (Qn) of the flip-flop. The $\bar{E}$ input is only required to be stable one set-up time prior to the LOW-to-HIGH transition for predictable operation.

For versions associated with the 74AHC377; 74AHCT377, refer to the following:

- For the master reset version, see 74AHC273; 74AHCT273
- For the transparent latch version, see 74AHC373; 74AHCT373
- For the 3-state version, see 74AHC374; 74AHCT374

2. Features

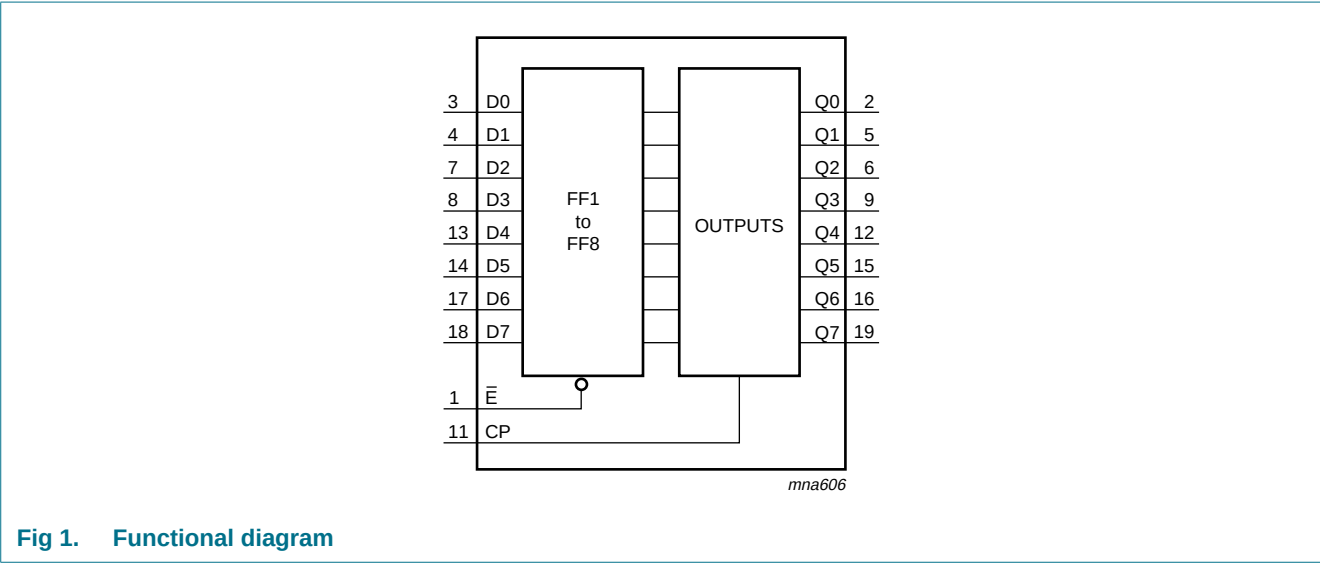
- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V_{CC}
- Ideal for addressable register applications
- Data enable for address and data synchronization
- Eight positive-edge triggered D-type flip-flops
- Input levels:
 - ◆ For 74AHC377: CMOS level
 - ◆ For 74AHCT377: TTL level
- ESD protection:
 - ◆ HBM EIA/JESD22-A114E exceeds 2000 V
 - ◆ MM EIA/JESD22-A115-A exceeds 200 V
 - ◆ CDM EIA/JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

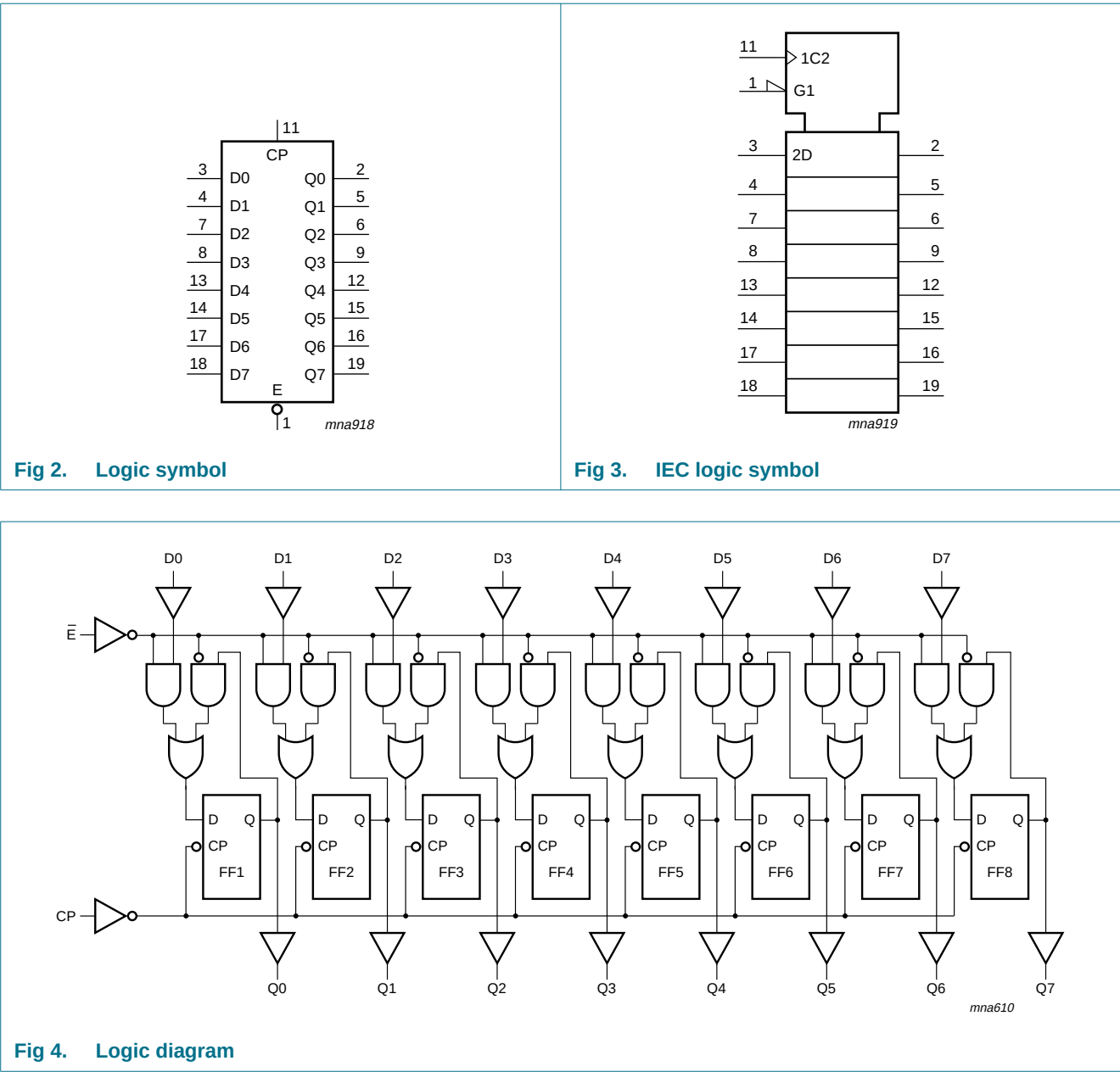
3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC377				
74AHC377D	−40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74AHC377PW	−40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74AHCT377				
74AHCT377D	−40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74AHCT377PW	−40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1

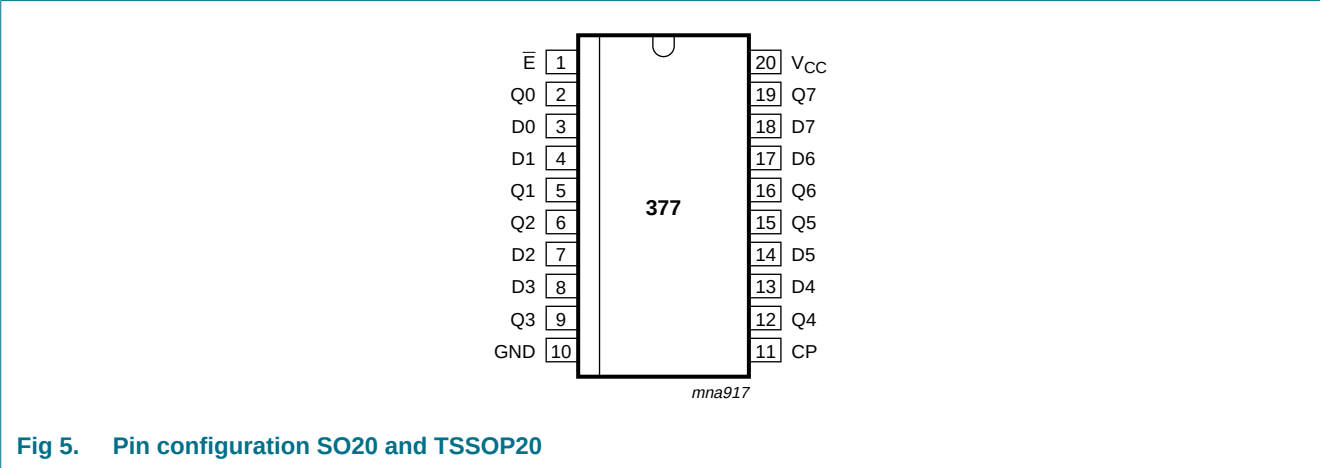
4. Functional diagram





5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$\bar{E}$	1	data enable input (active LOW)
Q0	2	flip-flop output
D0	3	data input
D1	4	data input
Q1	5	flip-flop output
Q2	6	flip-flop output
D2	7	data input
D3	8	data input
Q3	9	flip-flop output
GND	10	ground (0 V)
CP	11	clock input (LOW-to-HIGH, edge triggered)
Q4	12	flip-flop output
D4	13	data input
D5	14	data input
Q5	15	flip-flop output
Q6	16	flip-flop output
D6	17	data input
D7	18	data input
Q7	19	flip-flop output
V _{CC}	20	supply voltage

6. Functional description

Table 3. Function table^[1]

Operating mode	Control		Input	Output
	$\overline{E}$	CP	Dn	Qn
Load 1	L	↑	h	H
Load 0	L	↑	L	L
Hold (do nothing)	h	↑	X	no change
	H	X	X	no change

- [1] H = HIGH voltage level;
 h = HIGH voltage level one set-up time prior to the LOW-to-HIGH CP transition;
 L = LOW voltage level;
 L = LOW voltage level one set-up time prior to the LOW-to-HIGH CP transition;
 ↑ = LOW-to-HIGH CP transition;
 X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
V_I	input voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V	^[1] -20	-	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	^[1] -20	+20	mA
I_O	output current	$V_O = -0.5$ V to $(V_{CC} + 0.5$ V)	-25	+25	mA
I_{CC}	supply current		-	+75	mA
I_{GND}	ground current		-75	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	^[2] -	500	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 [2] For SO20 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.
 For TSSOP20 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.

8. Recommended operating conditions

Table 5. Operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74AHC377						
V _{CC}	supply voltage		2.0	5.0	5.5	V
V _I	input voltage		0	-	5.5	V
V _O	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		−40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 3.0 V to 3.6 V	-	-	100	ns/V
		V _{CC} = 4.5 V to 5.5 V	-	-	20	ns/V
74AHCT377						
V _{CC}	supply voltage		4.5	5.0	5.5	V
V _I	input voltage		0	-	5.5	V
V _O	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		−40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 4.5 V to 5.5 V	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC377										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = −50 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = −50 μA; V _{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I _O = −50 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = −4.0 mA; V _{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
V _{OL}	LOW-level output voltage	I _O = −8.0 mA; V _{CC} = 4.5 V	3.94	-	-	3.80	-	3.70	-	V
		V _I = V _{IH} or V _{IL}								
		I _O = 50 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I _O = 8.0 mA; V _{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I_I	input leakage current	$V_I = 5.5\text{ V}$ or GND; $V_{CC} = 0\text{ V}$ to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$; $V_{CC} = 5.5\text{ V}$	-	-	4.0	-	40	-	80	μA
C_I	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
74AHCT377										
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5\text{ V}$ to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5\text{ V}$ to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5\text{ V}$								
		$I_O = -50\text{ }\mu\text{A}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -8.0\text{ mA}$	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5\text{ V}$								
		$I_O = 50\text{ }\mu\text{A}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 8.0\text{ mA}$	-	-	0.36	-	0.44	-	0.55	V
I_I	input leakage current	$V_I = 5.5\text{ V}$ or GND; $V_{CC} = 0\text{ V}$ to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$; $V_{CC} = 5.5\text{ V}$	-	-	4.0	-	40	-	80	μA
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1\text{ V}$; other pins at V_{CC} or GND; $I_O = 0\text{ A}$; $V_{CC} = 4.5\text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C_I	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
74AHC377										
t _{pd}	propagation delay	CP to Qn; see Figure 6 ^[2]								
		V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	-	5.6	12.8	1.0	15.0	1.0	16.0	ns
		C _L = 50 pF	-	8.0	16.0	1.0	18.0	1.0	20.0	ns
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	3.9	9.0	1.0	10.5	1.0	11.5	ns
		C _L = 50 pF	-	5.6	10.5	1.0	12.0	1.0	13.5	ns
f _{max}	maximum frequency	see Figure 6								
		V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	80	125	-	70	-	70	-	MHz
		C _L = 50 pF	50	75	-	45	-	45	-	MHz
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	125	175	-	110	-	110	-	MHz
		C _L = 50 pF	85	120	-	75	-	75	-	MHz
t _W	pulse width	CP HIGH or LOW; see Figure 6								
		V _{CC} = 3.0 V to 3.6 V	5.0	-	-	5.0	-	5.0	-	ns
		V _{CC} = 4.5 V to 5.5 V	5.0	-	-	5.0	-	5.0	-	ns
t _{su}	set-up time	Dn, $\bar{E}$ to CP; see Figure 7								
		V _{CC} = 3.0 V to 3.6 V	5.0	-	-	5.0	-	5.0	-	ns
		V _{CC} = 4.5 V to 5.5 V	4.5	-	-	4.5	-	4.5	-	ns
t _h	hold time	Dn, $\bar{E}$ to CP; see Figure 7								
		V _{CC} = 3.0 V to 3.6 V	1.5	-	-	1.5	-	1.5	-	ns
		V _{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	ns
C _{PD}	power dissipation capacitance	f _i = 1 MHz; V _I = GND to V _{CC} ^[3]	-	20	-	-	-	-	-	pF

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
74AHCT377; V _{CC} = 4.5 V to 5.5 V										
t _{pd}	propagation delay	CP to Qn; see Figure 6								
		C _L = 15 pF	-	4.0	9.0	1.0	10.5	1.0	11.5	ns
		C _L = 50 pF	-	5.7	10.5	1.0	12.0	1.0	13.5	ns
f _{max}	maximum frequency	see Figure 6								
		C _L = 15 pF	90	140	-	80	-	80	-	MHz
		C _L = 50 pF	85	130	-	75	-	75	-	MHz
t _W	pulse width	CP HIGH or LOW; see Figure 6	5.0	-	-	5.0	-	5.0	-	ns
t _{su}	set-up time	Dn, $\overline{E}$ to CP; see Figure 7	4.5	-	-	4.5	-	4.5	-	ns
t _h	hold time	Dn, $\overline{E}$ to CP; see Figure 7	2.0	-	-	2.0	-	2.0	-	ns
C _{PD}	power dissipation capacitance	f _i = 1 MHz; V _I = GND to V _{CC}								
		[3]	-	23	-	-	-	-	-	pF

[1] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

11. Waveforms

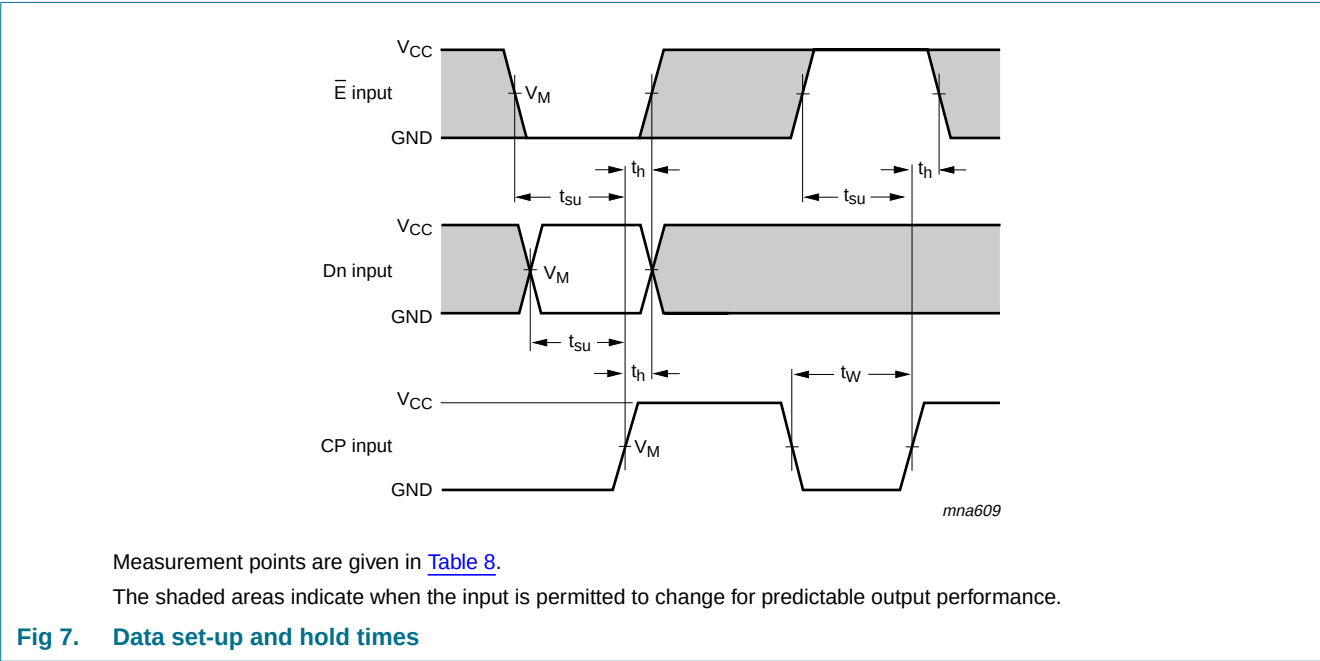
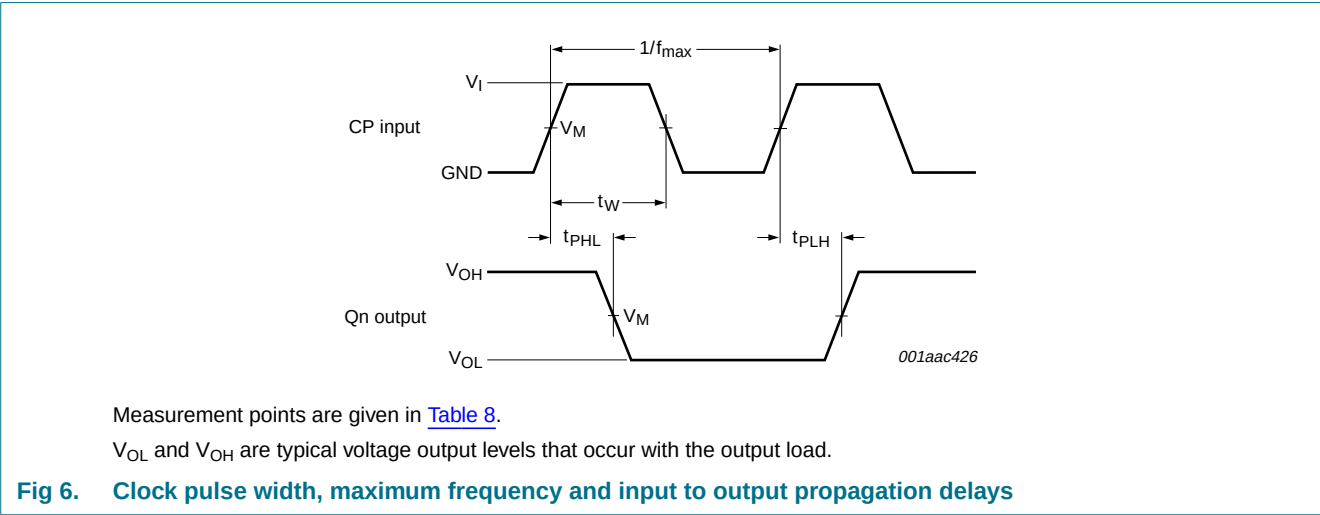
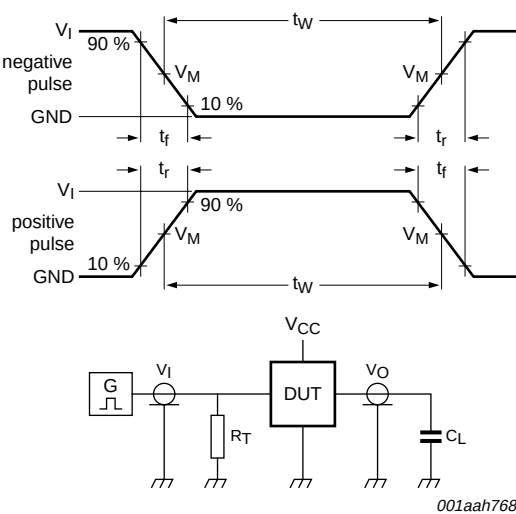


Table 8. Measurement points

Type	Input	Output
	V_M	V_M
74AHC377	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74AHCT377	1.5 V	$0.5 \times V_{CC}$



Test data is given in [Table 9](#).
Definitions test circuit:
 R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.
 C_L = load capacitance including jig and probe capacitance.

Fig 8. Load circuitry for measuring switching times

Table 9. Test data

Type	Input		Load	Test
	V_I	t_r, t_f	C_L	
74AHC377	V_{CC}	≤ 3.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}
74AHCT377	3.0 V	≤ 3.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mmSOT163-1

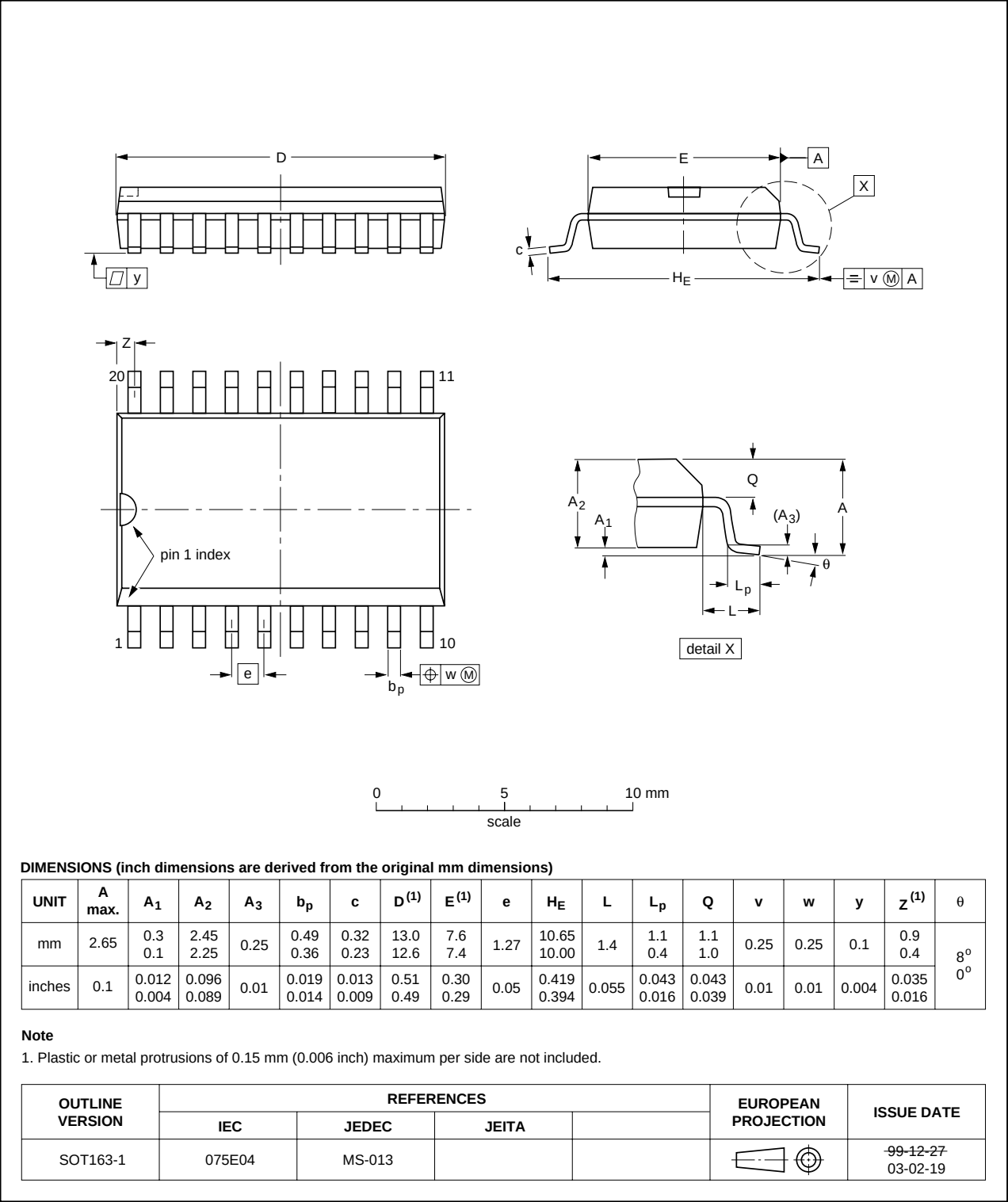


Fig 9. Package outline SOT163-1 (SO20)

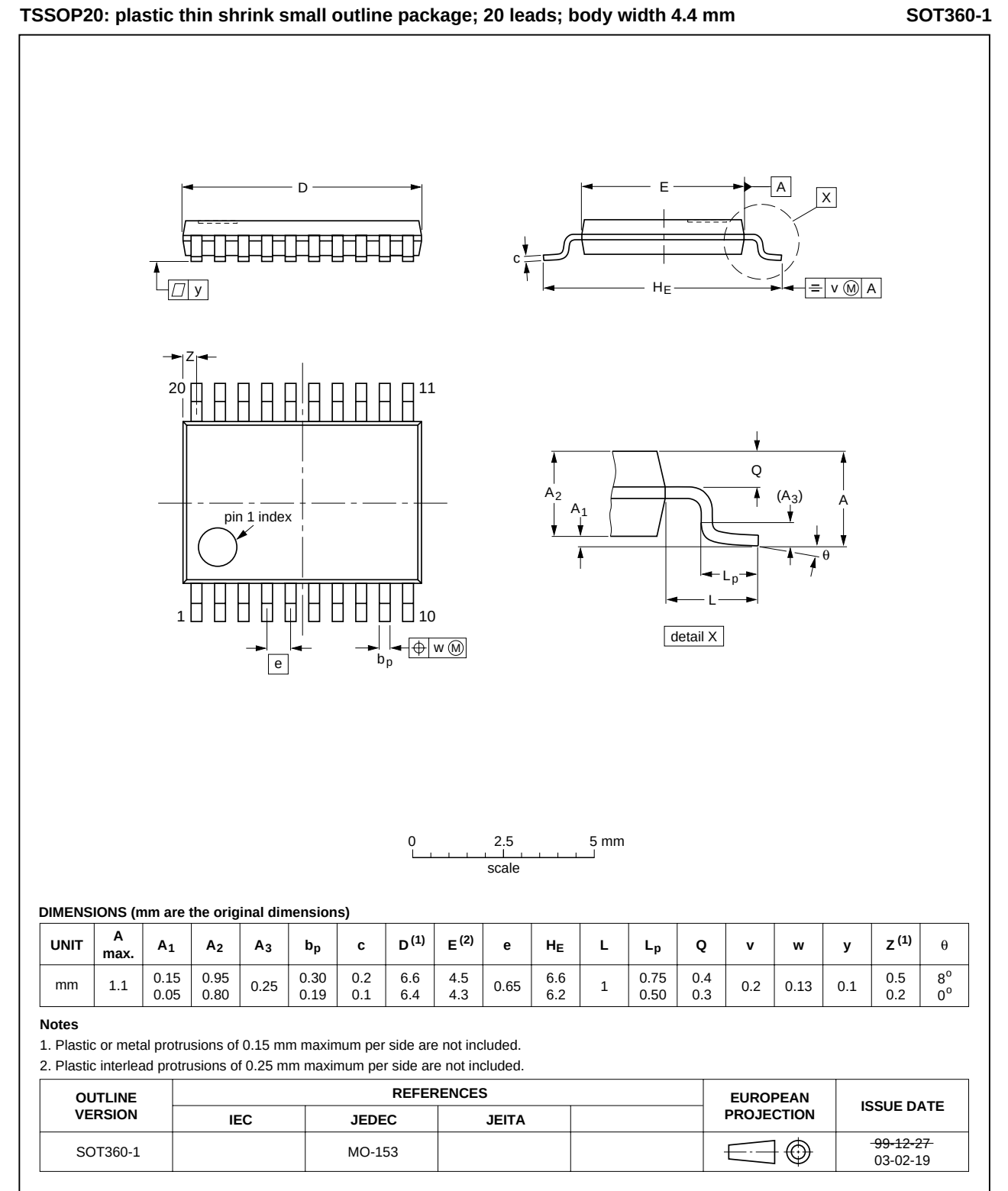


Fig 10. Package outline SOT360-1 (TSSOP20)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT377_2	20080612	Product data sheet	-	74AHC_AHCT377_1
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Table 6: the conditions for input leakage current have been changed.			
74AHC_AHCT377_1	20000815	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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